

## Vishay Semiconductors

## Silicon PIN Photodiode



### **DESCRIPTION**

BPV10 is a PIN photodiode with high speed and high sensitivity in clear, T-134 plastic package. It is sensitive to visible and near infrared radiation.

### **FEATURES**

· Package type: leaded • Package form: T-13/4

• Dimensions (in mm): Ø 5

· Leads with stand-off

· High photo sensitivity

· High sensitivity

· Suitable for visible and near infrared radiation

• Fast response times

• Angle of half sensitivity:  $\phi = \pm 20^{\circ}$ 

• Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



• High speed photo detector





HALOGEN

FREE **GREEN** 

| PRODUCT SUMMARY |                      |  |             |  |
|-----------------|----------------------|--|-------------|--|
| COMPONENT       | I <sub>ra</sub> (μΑ) | I <sub>ra</sub> (μA) φ (°) λ <sub>0.1</sub> (nm) |             |  |
| BPV10           | 70                   | ± 20   | 380 to 1100 |  |

#### Note

· Test condition see table "Basic Characteristics"

| ORDERING INFORMATION |           |                              |              |  |
|----------------------|-----------|------------------------------|--------------|--|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |  |
| BPV10                | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾         |  |

### Note

MOQ: minimum order quantity

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified) |  |                   |             |      |  |
|--|--|-------------------|-------------|------|--|
| PARAMETER  | TEST CONDITION                               | SYMBOL            | VALUE       | UNIT |  |
| Reverse voltage  |  | V <sub>R</sub>    | 60          | V    |  |
| Power dissipation  | T <sub>amb</sub> ≤ 25 °C                     | P <sub>V</sub>    | 215         | mW   |  |
| Junction temperature   |  | Tj                | 100         | °C   |  |
| Operating temperature range  |  | T <sub>amb</sub>  | -40 to +100 | °C   |  |
| Storage temperature range  |  | T <sub>stg</sub>  | -40 to +100 | °C   |  |
| Soldering temperature  | t ≤ 5 s, 2 mm from body                      | T <sub>sd</sub>   | 260         | °C   |  |
| Thermal resistance junction to ambient   | Connected with Cu wire, 0.14 mm <sup>2</sup> | R <sub>thJA</sub> | 350         | K/W  |  |

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| PARAMETER                      | TEST CONDITION  | SYMBOL            | MIN. | TYP.                  | MAX. | UNIT    |
|--------------------------------|---|-------------------|------|-----------------------|------|---------|
| Forward voltage                | I <sub>F</sub> = 50 mA  | $V_{F}$           | -    | 1.0                   | 1.3  | V       |
| Breakdown voltage              | I <sub>R</sub> = 100 μA, E = 0  | V <sub>(BR)</sub> | 60   | -                     | -    | V       |
| Reverse dark current           | V <sub>R</sub> = 20 V, E = 0  | I <sub>ro</sub>   | -    | 0.1                   | 5    | nA      |
| Diode capacitance              | V <sub>R</sub> = 0 V, f = 1 MHz, E = 0                                    | C <sub>D</sub>    | -    | 11                    | -    | pF      |
|                                | $V_R = 5 \text{ V, f} = 1 \text{ MHz, E} = 0$                             | C <sub>D</sub>    | -    | 3.8                   | -    | pF      |
| Open circuit voltage           | E <sub>A</sub> = 1 klx  | Vo                | =    | 480                   | -    | mV      |
|                                | $E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$                       | Vo                | -    | 450                   | -    | mV      |
| Short circuit current          | E <sub>A</sub> = 1 klx  | I <sub>K</sub>    | -    | 80                    | -    | μΑ      |
|                                | $E_e = 1 \text{ mW/cm}^2$ , $\lambda = 950 \text{ nm}$                    | Ι <sub>Κ</sub>    | =    | 65                    | -    | μA      |
| Reverse light current          | E <sub>A</sub> = 1 klx, V <sub>R</sub> = 5 V                              | I <sub>ra</sub>   | -    | 85                    | -    | μΑ      |
|                                | $E_e = 1 \text{ mW/cm}^2,  \lambda = 950 \text{ nm},$ $V_R = 5 \text{ V}$ | I <sub>ra</sub>   | 38   | 70                    | -    | μΑ      |
| Absolute spectral sensitivity  | $V_R = 5 \text{ V}, \ \lambda = 950 \text{ nm}$                           | s(λ)              | -    | 0.55                  | -    | A/W     |
| Angle of half sensitivity      |   | φ                 | -    | ± 20                  | -    | 0       |
| Wavelength of peak sensitivity |   | $\lambda_{p}$     | -    | 920                   | -    | nm      |
| Range of spectral bandwidth    |   | λ <sub>0.1</sub>  | -    | 380 to 1100           | -    | nm      |
| Quantum efficiency             | λ = 950 nm  | η                 | -    | 72                    | -    | %       |
| Noise equivalent power         | $V_R = 20 \text{ V}, \lambda = 950 \text{ nm}$                            | NEP               | -    | 3 x 10 <sup>-14</sup> | -    | W/√Hz   |
| Detectivity                    | $V_R = 20 \text{ V}, \lambda = 950 \text{ nm}$                            | D                 | -    | 3 x 10 <sup>12</sup>  | -    | cm√Hz/\ |
| Rise time                      | $V_R = 10 \text{ V}, R_L = 50 \Omega, \lambda = 830 \text{ nm}$           | t <sub>r</sub>    | -    | 80                    | -    | ns      |
| Fall time                      | $V_R = 10 \text{ V}, R_L = 50 \Omega, \lambda = 830 \text{ nm}$           | t <sub>f</sub>    | -    | 60                    | -    | ns      |

### **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

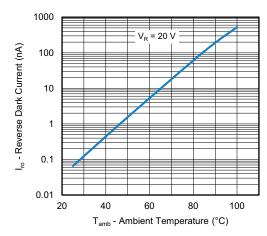


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

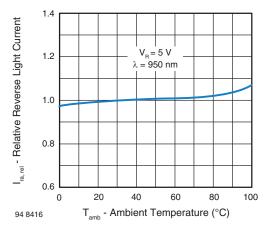


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

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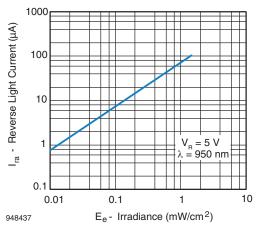


Fig. 3 - Reverse Light Current vs. Irradiance

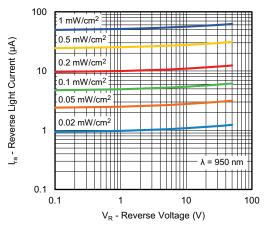


Fig. 4 - Reverse Light Current vs. Reverse Voltage

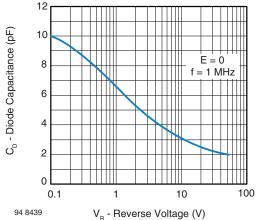


Fig. 5 - Diode Capacitance vs. Reverse Voltage

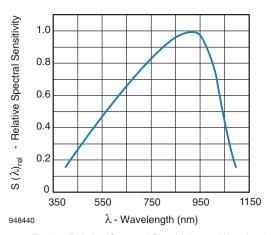


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

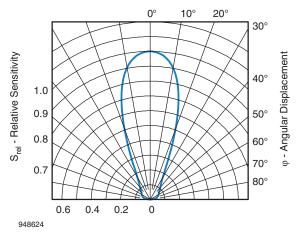
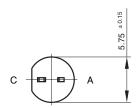
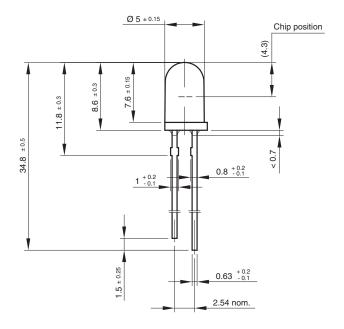


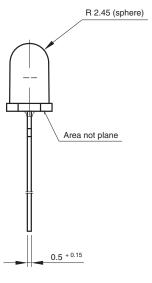
Fig. 7 - Relative Sensitivity vs. Angular Displacement



### **PACKAGE DIMENSIONS** in millimeters







technical drawings

according to DIN specifications

Drawing-No.: 6.544-5185.02-4

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